

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant :	Satoru Okamoto	Art Unit :	1765
Serial No. :	10/689,617	Examiner :	Mahmoud Dahimene
Filed :	October 22, 2003	Conf. No. :	4799
Title :	METHOD FOR CLEANING PLASMA ETCHING APPARATUS, METHOD FOR PLASMA ETCHING, AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE		

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

REPLY TO ACTION OF NOVEMBER 2, 2006

In reply to the Office Action of November 2, 2006, applicant submits the following remarks.

Claims 1-95 are pending, with claims 1, 8, 15, 22, 29, 36, 43, 50, 57, 64, 71, 78, and 85 being independent. Applicant acknowledges with appreciation the Examiner's allowance of claims 85-95.

Claim Rejections – 35 U.S.C. §112

Claim 1 has been rejected due to an alleged failure of the specification to comply with the written description requirement with respect to the feature "not to form a semiconductor device." Applicant requests withdrawal of this rejection because the application describes in detail a second substrate that is placed in the chamber but that is not to form a semiconductor device, and such description is sufficient that one skilled in the art can reasonably conclude that the inventor had possession of the claimed invention. See MPEP 2163 I. In particular, the application describes a first substrate 7001 that is used for forming a semiconductor device and a second substrate (a dummy substrate) that is set on the stage during cleaning of the chamber. See the Specification at page 14, lines 1-8; page 18, lines 3-7; and Fig. 3A. It is clear from at least this portion of the description that the dummy substrate is distinct from the first substrate 7001 and that the dummy substrate is not to form the semiconductor device.